

Product Summary

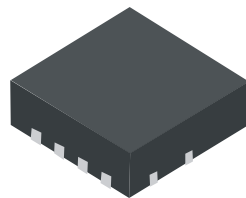
BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-30V	6mΩ @ V _{GS} = -10V	-70A
	13mΩ @ V _{GS} = -4.5V	-45A

Description

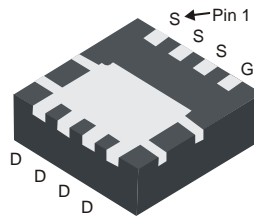
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

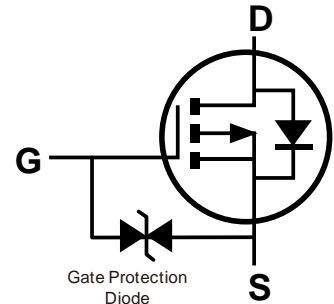
- Backlighting
- Power Management Functions
- DC-DC Converters



Top View



Bottom View



Equivalent Circuit

Features and Benefits

- Low R_{DS(ON)} – Ensures on State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied By SO-8 Enabling Smaller End Product
- ESD Protected Gate
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**

Mechanical Data

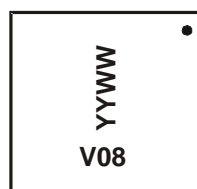
- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.030 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3007SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMP3007SFG-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



V08= Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 16 = 2016)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-30	V	
Gate-Source Voltage	V _{GSS}	±25	V	
Continuous Drain Current (Note 7) V _{GS} = -10V	I _D	T _C = +25°C	-70	A
		T _C = +70°C	-55	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-3.0	A	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	-120	A	
Avalanche Current (Notes 8) L = 1mH	I _{AS}	-16	A	
Avalanche Energy (Notes 8) L = 1mH	E _{AS}	130	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)		Steady State	R _{θJA}	105
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)		Steady State	R _{θJA}	45
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	3.0	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	4.3	6	mΩ	V _{GS} = -10V, I _D = -11.5A
		—	6.6	13		V _{GS} = -4.5V, I _D = -8.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iSS}	—	2826	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	606	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	305	—	pF	
Gate Resistance	R _g	—	23	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	31.2	—	nC	V _{DS} = -15V, I _D = -11.5A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	64.2	—	nC	
Gate-Source Charge	Q _{gs}	—	10.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	11.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.8	—	ns	V _{DD} = -15V, V _{GS} = -10V, R _g = 6Ω, I _D = -11.5A
Turn-On Rise Time	t _R	—	4.3	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	306	—	ns	
Turn-Off Fall Time	t _F	—	125	—	ns	
Reverse Recovery Time	t _{RR}	—	19	—	ns	
Reverse Recovery Charge	Q _{RR}	—	9.8	—	nC	I _S = -11.5A, dI/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

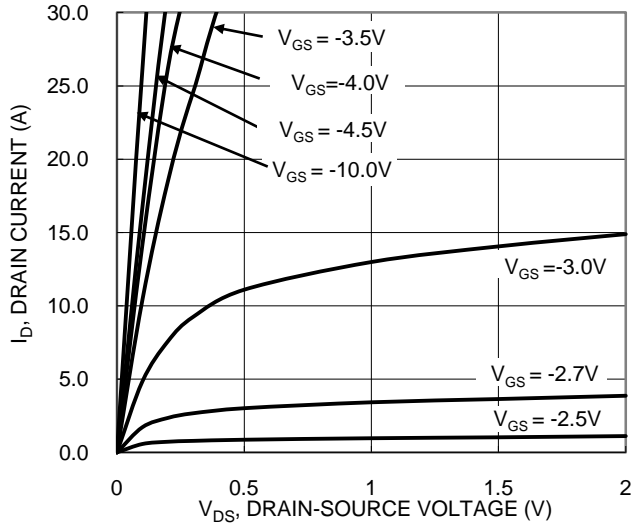


Figure 1. Typical Output Characteristic

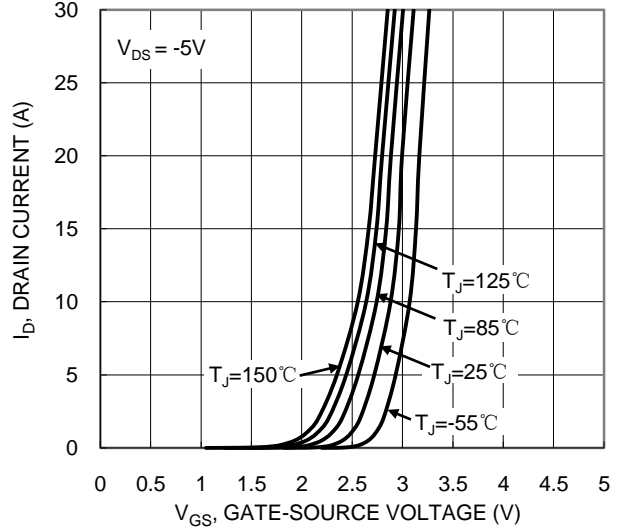


Figure 2. Typical Transfer Characteristic

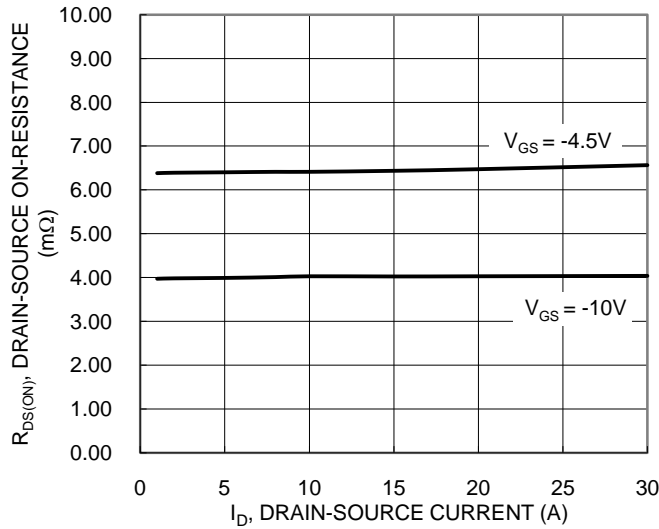


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

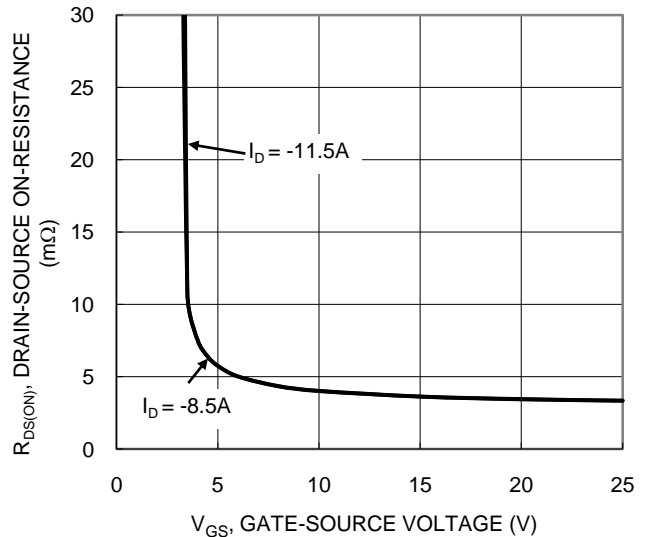


Figure 4. Typical Transfer Characteristic

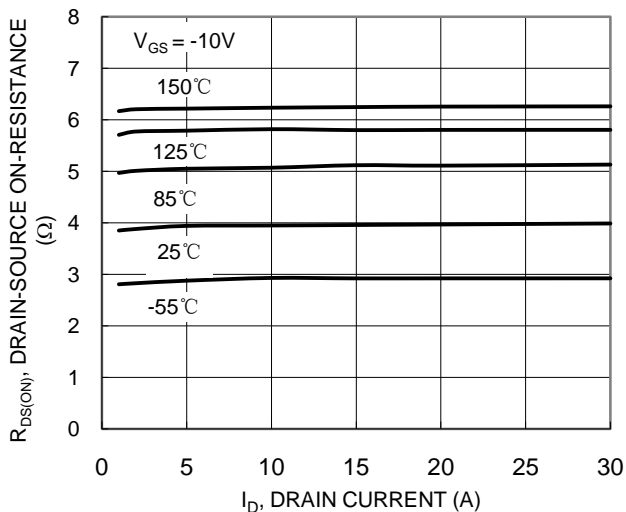


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

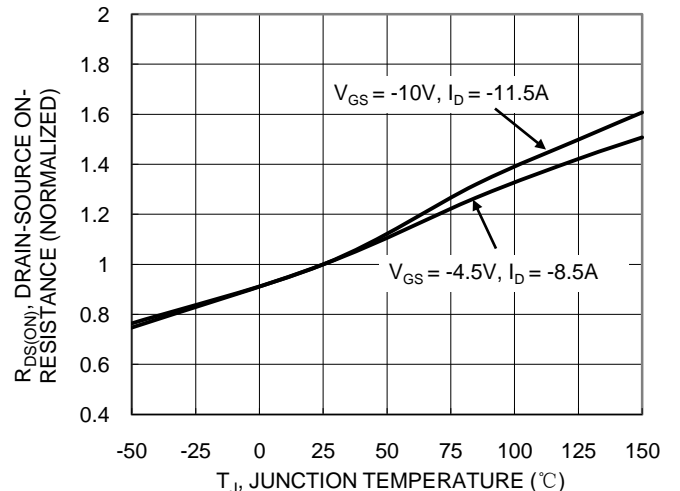


Figure 6. On-Resistance Variation with Temperature

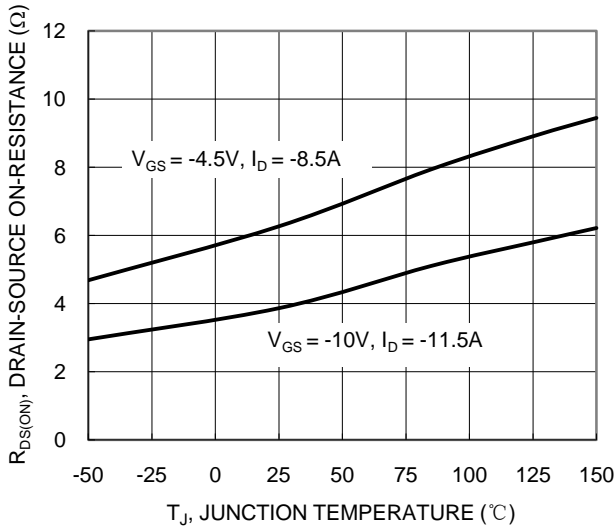


Figure 7. On-Resistance Variation with Temperature

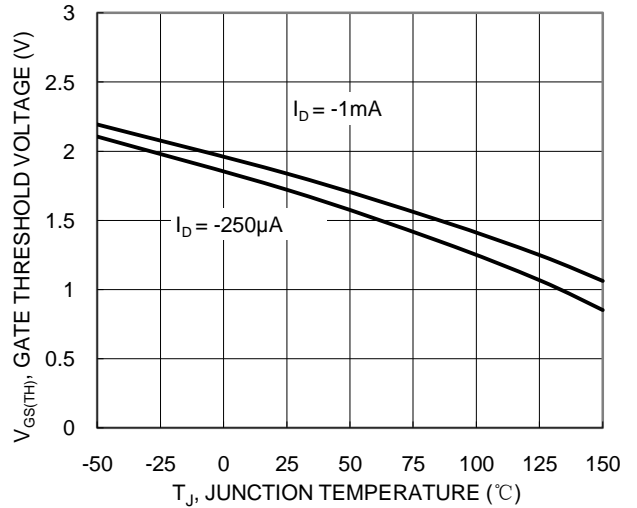


Figure 8. Gate Threshold Variation vs. Junction Temperature

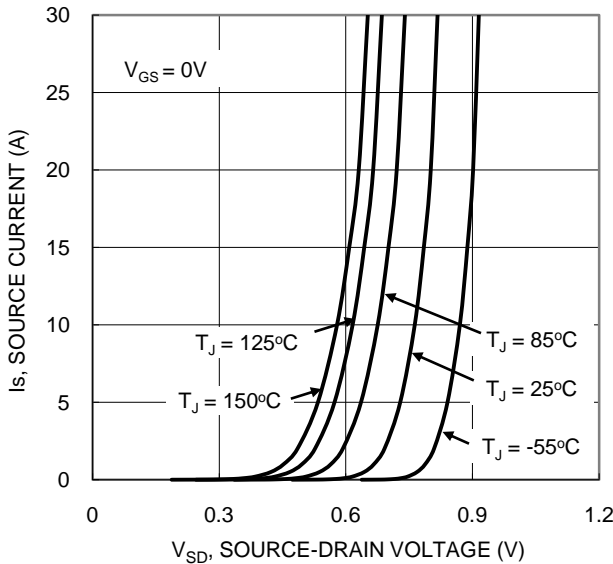


Figure 9. Diode Forward Voltage vs. Current

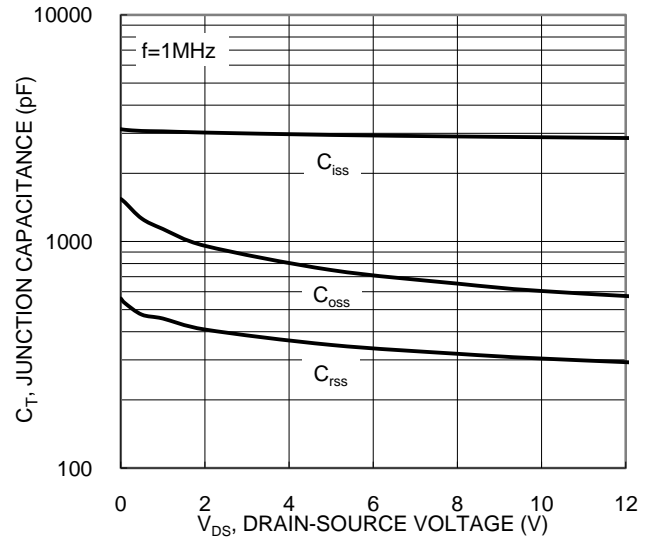


Figure 10. Typical Junction Capacitance

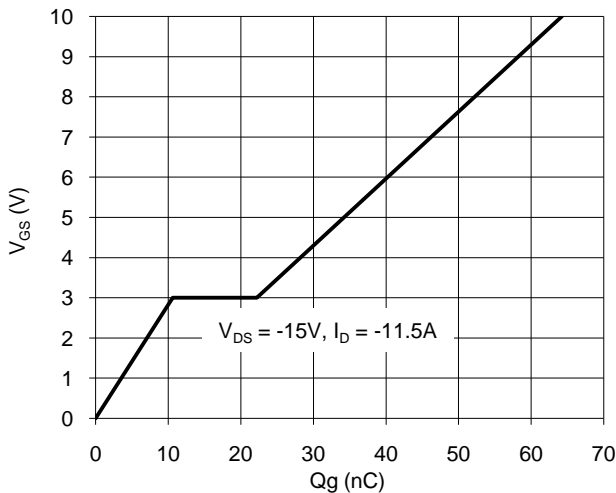


Figure 11. Gate Charge

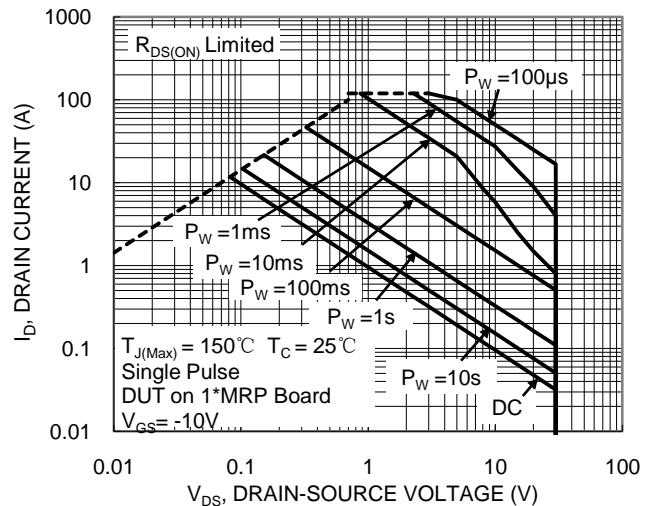


Figure 12. SOA, Safe Operation Area

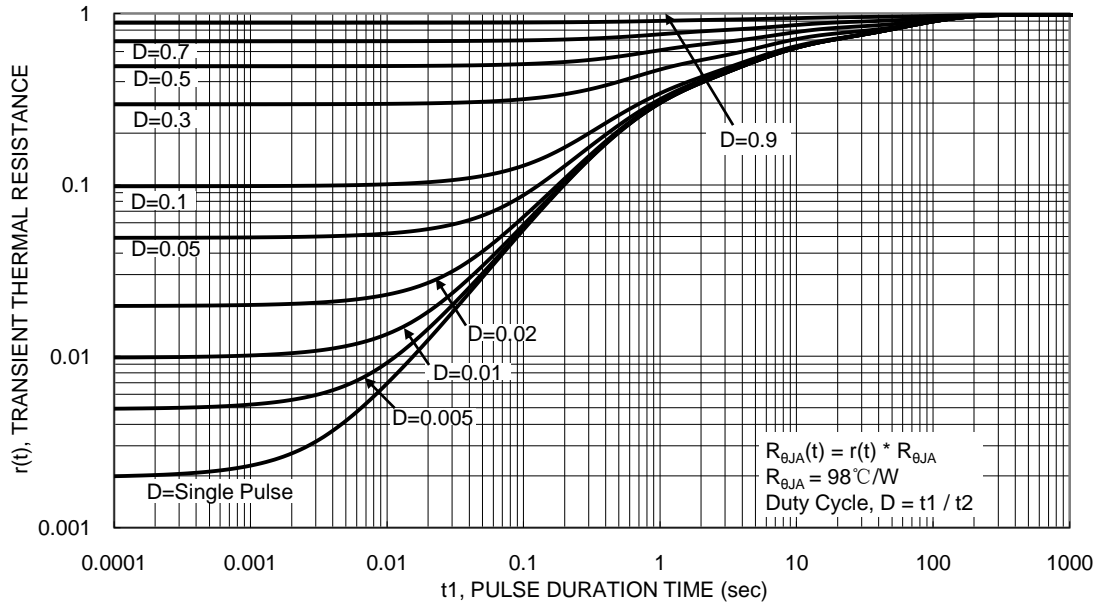
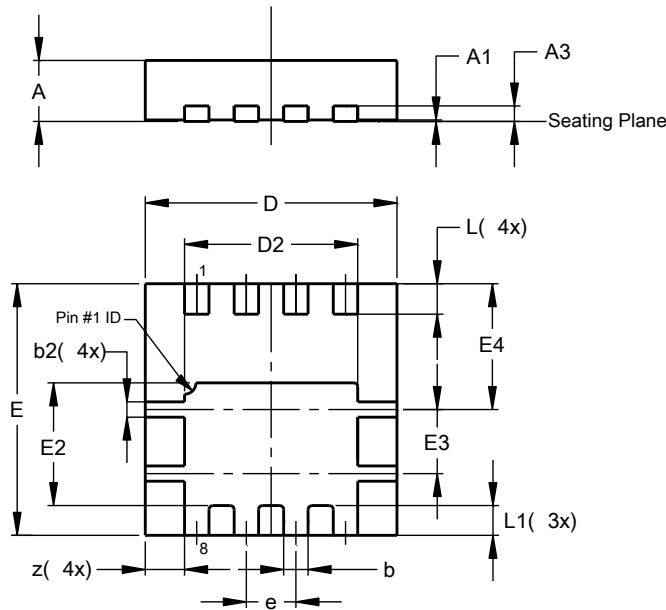


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

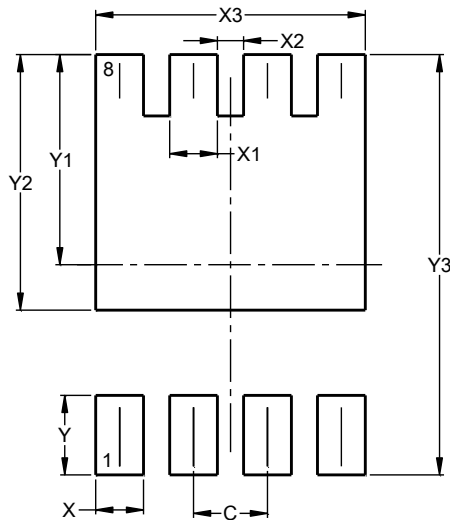


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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